

Silicon PNP Power Transistors

2SA885

DESCRIPTION

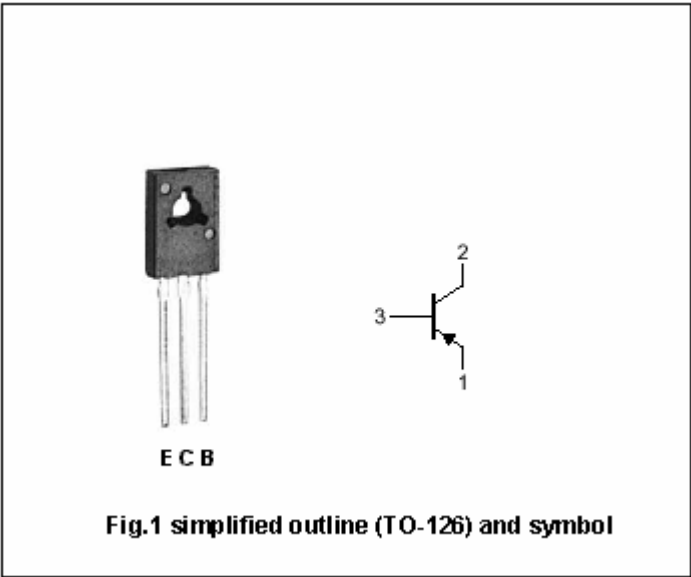
- With TO-126 package
- Complement to type 2SC1846
- Low collector-emitter saturation voltage

APPLICATIONS

- For low-frequency power amplification

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute Maximun Ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-45	V
V_{CEO}	Collector-emitter voltage	Open base	-35	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-1	A
I_{CM}	Collector current-peak		-1.5	A
P_C	Collector power dissipation	$T_C=25$	1.2^{*1}	W
			5^{*2}	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

Note) *1: Without heat sink

*2: With a 100 × 100 × 2 mm A1 heat sink

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-2mA; I _B =0	-35			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-10 μA; I _E =0	-45			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.5A; I _B =-50mA			-0.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-20V; I _E =0			-0.1	μA
I _{CEO}	Collector cut-off current	V _{CE} =-20V; I _B =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μA
h _{FE-1}	DC current gain	I _C =-0.5A; V _{CE} =-10V	85		340	
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-5V	50			
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		20	30	pF
f _T	Transition frequency	I _C =50mA; V _{CB} =-10V; f=200MHz		200		MHz

◆ h_{FE-1} Classifications

Q	R	S
85-170	120-240	170-340

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PACKAGE OUTLINE

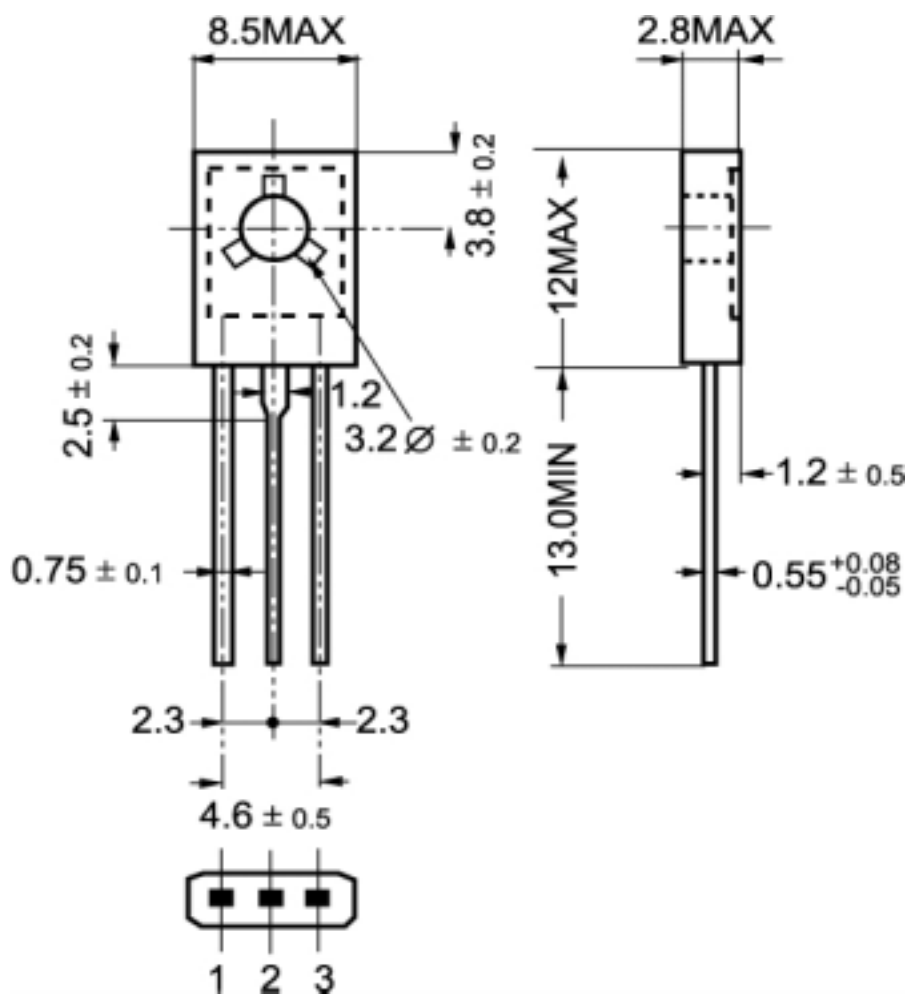
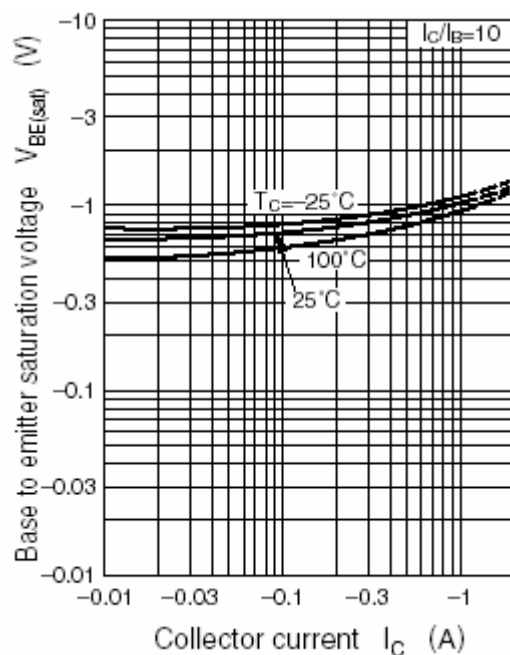
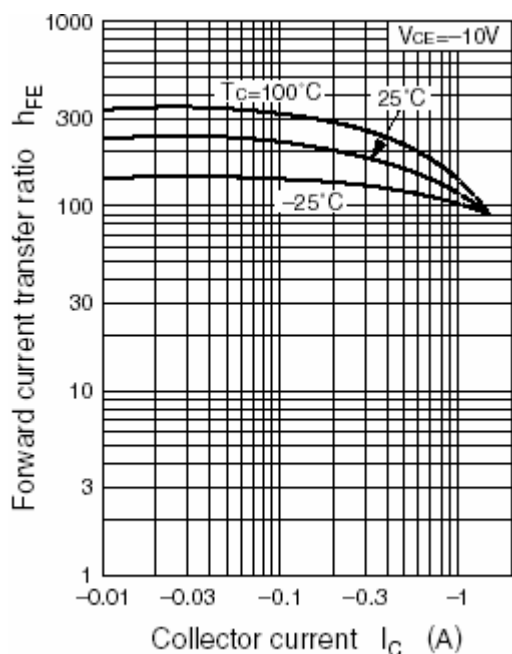
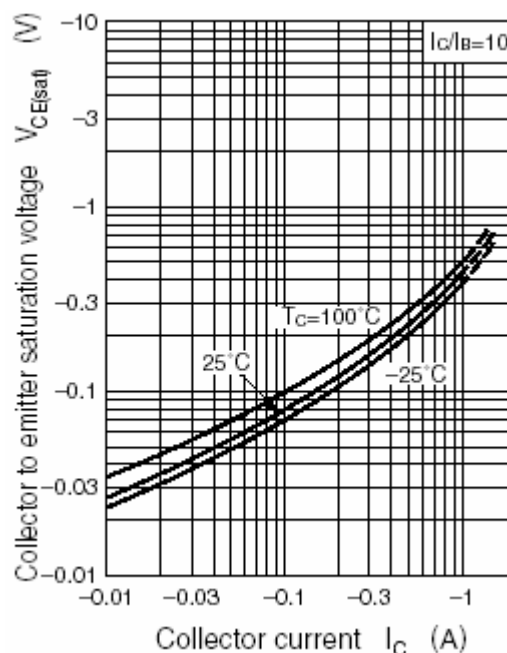
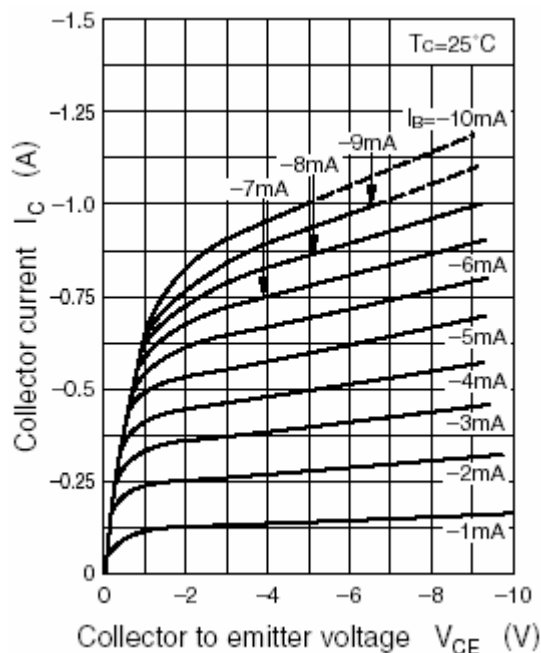


Fig.2 Outline dimensions

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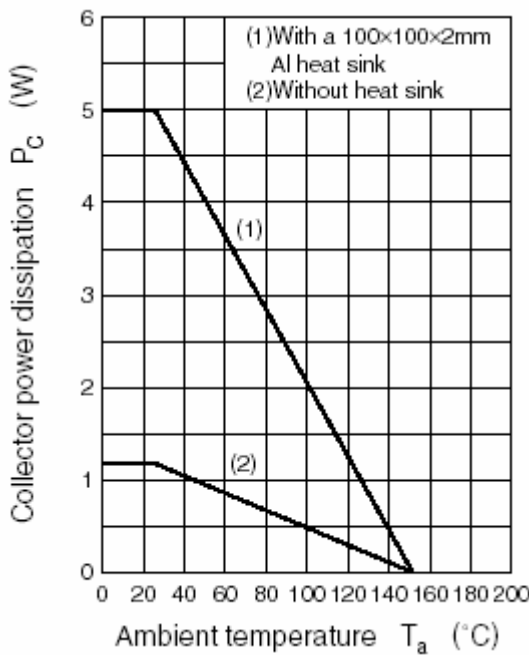


Fig.7 Power Derating

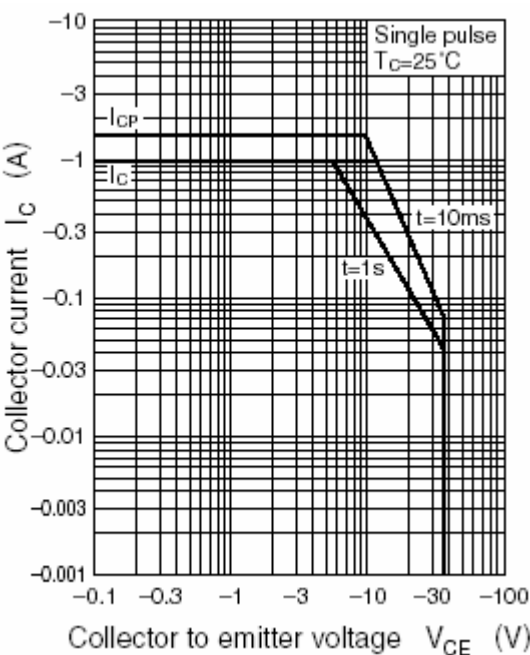


Fig.8 Safe Operating Area